HALOGEN

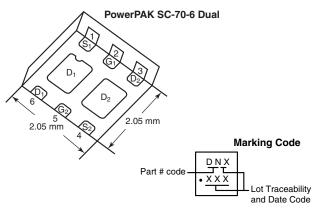
FREE



Vishay Siliconix

Dual P-Channel 30-V (D-S) MOSFET

| PRODUCT SUMMARY | | | | | | | | | |
|---------------------|------------------------------------|--------------------|-----------------------|--|--|--|--|--|--|
| V _{DS} (V) | $R_{DS(on)}$ (Ω) Max. | I _D (A) | Q _g (Typ.) | | | | | | |
| - 30 | 0.064 at V _{GS} = - 10 V | - 4.5 ^a | | | | | | | |
| | 0.078 at $V_{GS} = -4.5 \text{ V}$ | - 4.5 ^a | 6.6 nC | | | | | | |
| | 0.120 at V _{GS} = - 2.5 V | - 4.5 ^a | | | | | | | |



Ordering Information:

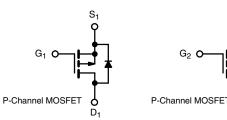
SiA929DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Gen III Power MOSFET
- Thermally Enhanced PowerPAK® SC-70 Package
 - Small Footprint Area
 - Low On-Resistance
- 100 % R_a Tested
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- Load Switch and Battery Management for Smart Phones, Tablet PCs and Portable Media Players
- Fast Battery Charging



| Parameter | | Symbol | Limit | Unit | |
|---|------------------------|-----------------------------------|-----------------------|------|--|
| Drain-Source Voltage | | V _{DS} | - 30 | V | |
| Gate-Source Voltage | | V _{GS} | ± 12 | | |
| | T _C = 25 °C | | - 4.5 ^a | | |
| Continuous Drain Current (T _{.I} = 150 °C) | T _C = 70 °C | | - 4.5 ^a | | |
| Continuous Diam Current (1) = 130 °C) | T _A = 25 °C | I _D | - 4.3 ^{b, c} | Α | |
| | T _A = 70 °C | | - 3.4 ^{b, c} | | |
| Pulsed Drain Current (t = 300 μs) | 1 | I _{DM} | - 15 | 7 | |
| Continuous Source-Drain Diode Current | T _C = 25 °C | I_ | - 4.5 ^a | | |
| Continuous Source-Drain Diode Current | T _A = 25 °C | I _S | - 1.6 ^{b, c} | İ | |
| | T _C = 25 °C | | 7.8 | w | |
| Maximum Dawar Dissipation | T _C = 70 °C | P _D | 5 | | |
| Maximum Power Dissipation | T _A = 25 °C | ' D | 1.9 ^{b, c} | VV | |
| | T _A = 70 °C | | 1.2 ^{b, c} | | |
| Operating Junction and Storage Temperature Ra | ange | T _J , T _{stg} | - 55 to 150 | °C | |
| Soldering Recommendations (Peak Temperature | e) ^{d, e} | | 260 | | |

| THERMAL RESISTANCE RATINGS | | | | | | | | | |
|---|--------------|-------------------|---------|---------|-------|--|--|--|--|
| Parameter | | Symbol | Typical | Maximum | Unit | | | | |
| Maximum Junction-to-Ambient ^{b, f} | t ≤ 5 s | R _{thJA} | 52 | 65 | °C/W | | | | |
| Maximum Junction-to-Case (Drain) | Steady State | R _{thJC} | 12.5 | 16 | O/ VV | | | | |

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- d. See Solder Profile (www.vishav.com/ppg?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under Steady State conditions is 110 °C/W.

Document Number: 63398 S11-1654-Rev. A, 15-Aug-11

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| Parameter | Symbol | Test Conditions | Min. | Тур. | Max. | Unit |
|---|-------------------------|--|-------|--------|-------|-------|
| Static | - | | | | l | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$ | - 30 | | | V |
| V _{DS} Temperature Coefficient | $\Delta V_{DS}/T_{J}$ | I _D = - 250 μA | | - 23 | | mV/°C |
| V _{GS(th)} Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | I _D = - 250 μA | | 1.5 | | |
| Gate-Source Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$ | - 0.6 | | - 1.1 | V |
| Gate-Source Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$ | | | ± 100 | nA |
| 7 0 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 | | V _{DS} = - 30 V, V _{GS} = 0 V | | | - 1 | μΑ |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$ | | | - 10 | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$ | - 10 | | | Α |
| | ` ' | V _{GS} = - 10 V, I _D = - 3 A | | 0.052 | 0.064 | Ω |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = - 4.5 V, I _D = - 2 A | | 0.062 | 0.078 | |
| | , , | V _{GS} = - 2.5 V, I _D = - 1 A | | 0.090 | 0.120 | |
| Forward Transconductance ^a | 9 _{fs} | V _{DS} = - 15 V, I _D = - 3 A | | 10 | | S |
| Dynamic ^b | | | | | | |
| Input Capacitance | C _{iss} | | | 575 | | |
| Output Capacitance | C _{oss} | V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz | | 60 | | pF |
| Reverse Transfer Capacitance | C _{rss} | , do , | | 51 | | |
| · | | V _{DS} = - 15 V, V _{GS} = - 10 V, I _D = - 4.3 A | | 14 | 21 | |
| Total Gate Charge | Q_g | 20 | | 6.6 | 10 | 1 |
| Gate-Source Charge | Q _{gs} | V _{DS} = - 15 V, V _{GS} = - 4.5 V, I _D = - 4.3 A | | 1.2 | | nC |
| Gate-Drain Charge | Q _{gd} | 30 | | 1.9 | | |
| Gate Resistance | R_g | f = 1 MHz | 1.1 | 5.5 | 11 | Ω |
| Turn-On Delay Time | t _{d(on)} | | | 15 | 30 | |
| Rise Time | t _r | $V_{DD} = -15 \text{ V}, R_1 = 4.4 \Omega$ | | 18 | 35 | - |
| Turn-Off Delay Time | t _{d(off)} | $I_D \cong -3.4 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$ | | 22 | 40 | |
| Fall Time | t _f | _ | | 10 | 20 | |
| Turn-On Delay Time | t _{d(on)} | | | 5 | 10 | ns |
| Rise Time | t _r | $V_{DD} = -15 \text{ V}, R_1 = 4.4 \Omega$ | | 10 | 20 | 1 |
| Turn-Off Delay Time | t _{d(off)} | | | 22 | 40 | _ |
| Fall Time | | | | 10 | 20 | |
| Drain-Source Body Diode Characterist | ics | | | | | |
| Continuous Source-Drain Diode Current | I _S | T _C = 25 °C | | | - 4.5 | |
| Pulse Diode Forward Current | I _{SM} | | | | - 15 | A |
| Body Diode Voltage | V_{SD} | I _S = - 3.4 A, V _{GS} = 0 V | | - 0.89 | - 1.2 | ٧ |
| Body Diode Reverse Recovery Time | t _{rr} | | | 20 | 40 | ns |
| Body Diode Reverse Recovery Charge | Q _{rr} | | | 10 | 20 | nC |
| Reverse Recovery Fall Time | t _a | $I_F = -3.4 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$ | | 9 | | ns |
| Reverse Recovery Rise Time | t _b | | | 11 | 1 | |

Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

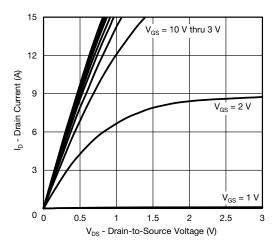
a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

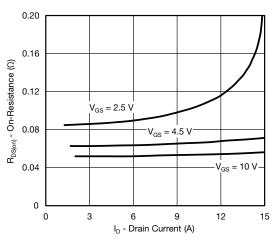


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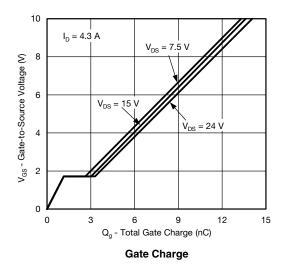
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

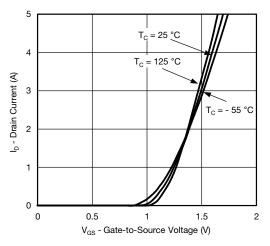


Output Characteristics

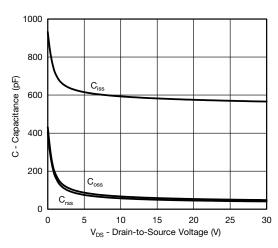


On-Resistance vs. Drain Current and Gate Voltage

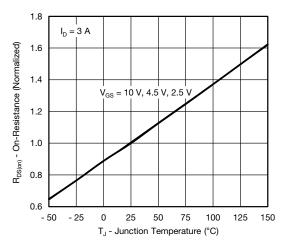




Transfer Characteristics



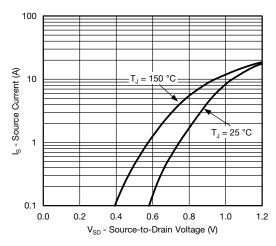
Capacitance



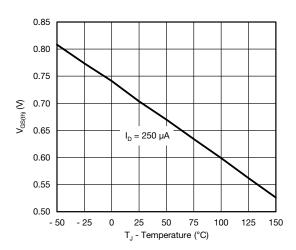
On-Resistance vs. Junction Temperature

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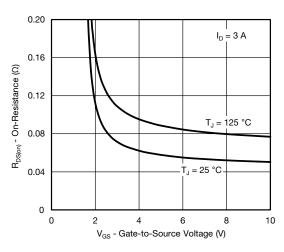
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



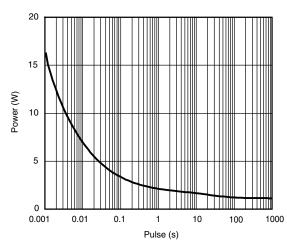
Soure-Drain Diode Forward Voltage



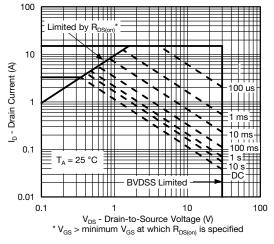
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient

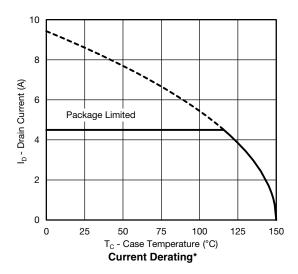


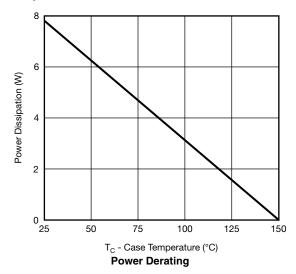
Safe Operating Area, Junction-to-Ambient



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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



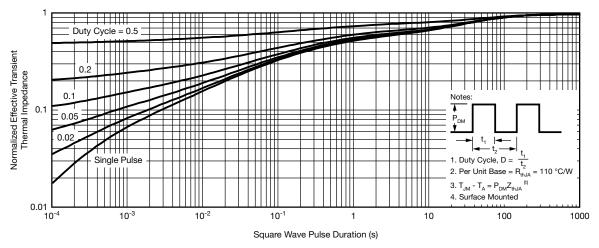


^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

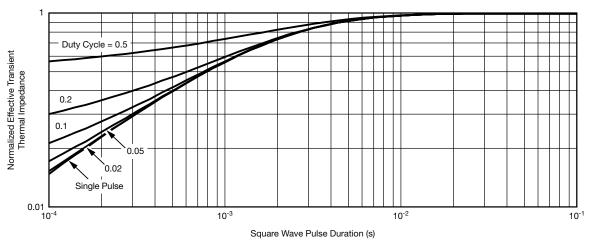
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

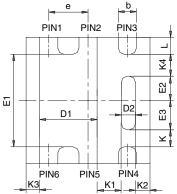
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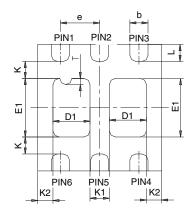




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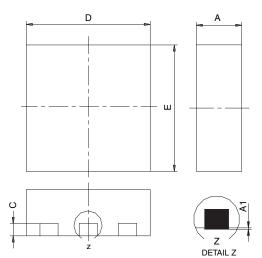
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

| | | | SINGL | E PAD | | | | | DUAI | L PAD | | | |
|-----------|---------------------|---------------------|-----------|---------------------|---------------------|-------|----------|-----------|-------|-----------|--------|-------|--|
| DIM | M | ILLIMETER | RS | | INCHES | | M | ILLIMETER | RS | | INCHES | | |
| | Min | Nom | Max | Min | Nom | Max | Min | Nom | Max | Min | Nom | Max | |
| Α | 0.675 | 0.75 | 0.80 | 0.027 | 0.030 | 0.032 | 0.675 | 0.75 | 0.80 | 0.027 | 0.030 | 0.032 | |
| A1 | 0 | - | 0.05 | 0 | - | 0.002 | 0 | - | 0.05 | 0 | - | 0.002 | |
| b | 0.23 | 0.30 | 0.38 | 0.009 | 0.012 | 0.015 | 0.23 | 0.30 | 0.38 | 0.009 | 0.012 | 0.015 | |
| С | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 | |
| D | 1.98 | 2.05 | 2.15 | 0.078 | 0.081 | 0.085 | 1.98 | 2.05 | 2.15 | 0.078 | 0.081 | 0.085 | |
| D1 | 0.85 | 0.95 | 1.05 | 0.033 | 0.037 | 0.041 | 0.513 | 0.613 | 0.713 | 0.020 | 0.024 | 0.028 | |
| D2 | 0.135 | 0.235 | 0.335 | 0.005 | 0.009 | 0.013 | | | | | | | |
| Е | 1.98 | 2.05 | 2.15 | 0.078 | 0.081 | 0.085 | 1.98 | 2.05 | 2.15 | 0.078 | 0.081 | 0.085 | |
| E1 | 1.40 | 1.50 | 1.60 | 0.055 | 0.059 | 0.063 | 0.85 | 0.95 | 1.05 | 0.033 | 0.037 | 0.041 | |
| E2 | 0.345 | 0.395 | 0.445 | 0.014 | 0.016 | 0.018 | | | | | | | |
| E3 | 0.425 | 0.475 | 0.525 | 0.017 | 0.019 | 0.021 | | | | | | | |
| е | | 0.65 BSC | | | 0.026 BSC | , | 0.65 BSC | | | 0.026 BSC | | | |
| K | 0.275 TYP 0.011 TYP | | | 0.275 TYP 0.011 TYP | | | | | | | | | |
| K1 | 0.400 TYP 0.016 T | | 0.016 TYP | | 0.320 TYP | | | 0.013 TYP | | | | | |
| K2 | 0.240 TYP 0.009 | | 0.009 TYP | | 0.252 TYP 0.010 TYP | | | | | | | | |
| К3 | | 0.225 TYP | 1 | 0.009 TYP | | | | | | | | | |
| K4 | | 0.355 TYP 0.014 TYP | | | | | | | | | | | |
| L | 0.175 | 0.275 | 0.375 | 0.007 | 0.011 | 0.015 | 0.175 | 0.275 | 0.375 | 0.007 | 0.011 | 0.015 | |
| Т | | | | | | | 0.05 | 0.10 | 0.15 | 0.002 | 0.004 | 0.006 | |
| ECNI- C C | 7404 D | . 0 00 1 | . 07 | | | | | | | | | | |

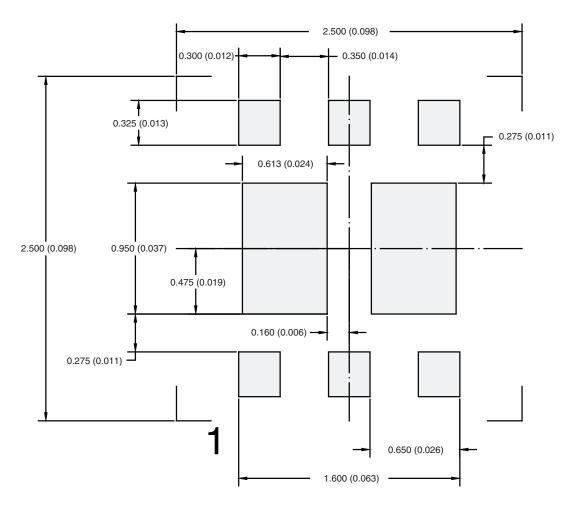
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

Document Number: 73001 06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual



Dimensions in mm (inches)

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Revision: 02-Oct-12 Document Number: 91000

AMEYA360 Components Supply Platform

Authorized Distribution Brand:

























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